

(19)
(12)

(KR)
(A)

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2001 - 0083653
2001 09 01

(21) 10 - 2000 - 0007647
(22) 2000 02 17

(71)

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(72)

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555

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(74)

1

(54)

.. . . . (MCVD)

가 , 가 , 가 , 가 ,

가

1

3

¹ ¹ ,

2 MCVD

3 1 .

*

110 : 120 : 1

130 : 1

150 : 가

(Modified Chemical Vapor Deposition, MCVD)

MCVD

(Outside Vapour Deposition, MCVD, OVD) (Vapour Axial Deposition, VAD)

1 , 1 , 1 (clad)(10) (Collapsing) (Core) (11) 가

2 MCVD, (core) (Substrate Tub
e, quartz)(60) SiCl₄, GeCl₄, O₂(53)
가 가 SiO₂, GeO₂ (60), (61a) (Collapse) 1
, (clad) 1 2 (61b)
2 (61b)

1 MCVD (Collapsing) 1 . (61a, 61b)

) (153) (Deposition), 가 (SiCl₄, GeCl₄, O₂)
), (140), 가, 가 (153) 가
) (130)

- (Pinch - Off) , 1 (120) .
, , 1
(softening point) .

(57)

1.

1

가 ,
가 2 : 가

3

2.

1 , 2

가

3.

1 , 2

가

가

4.

1 , 3

1 ;

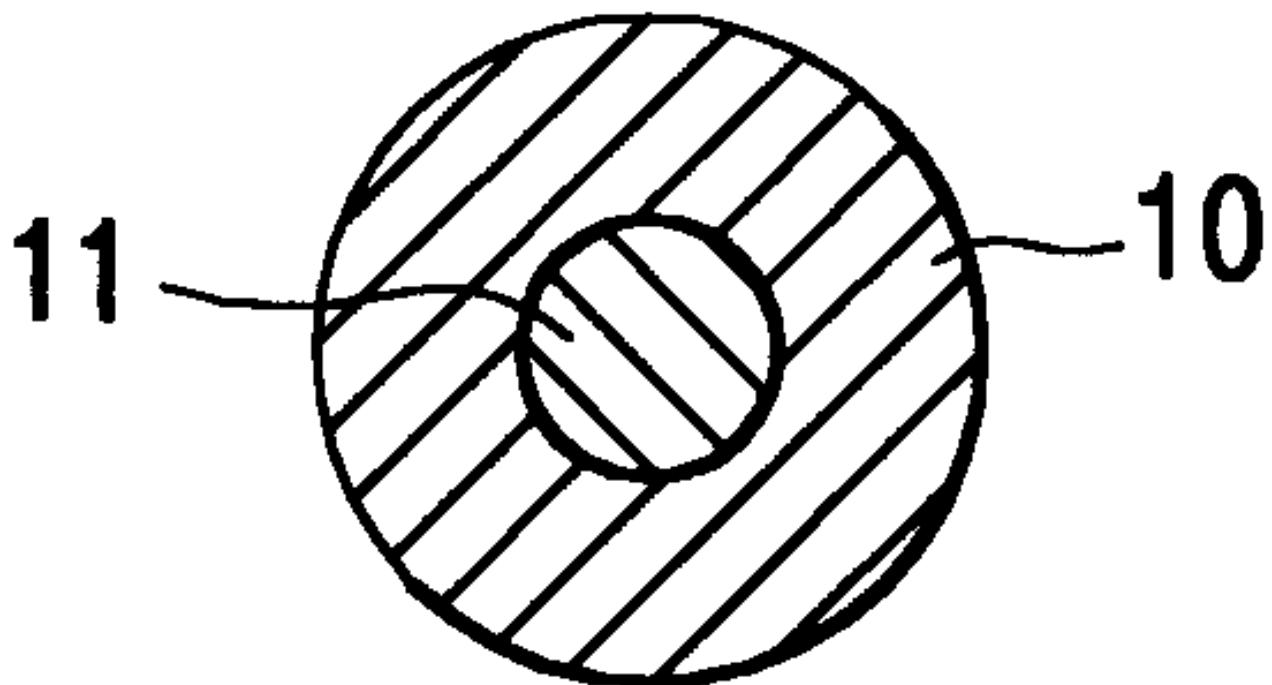
가

(Pinch - Off)

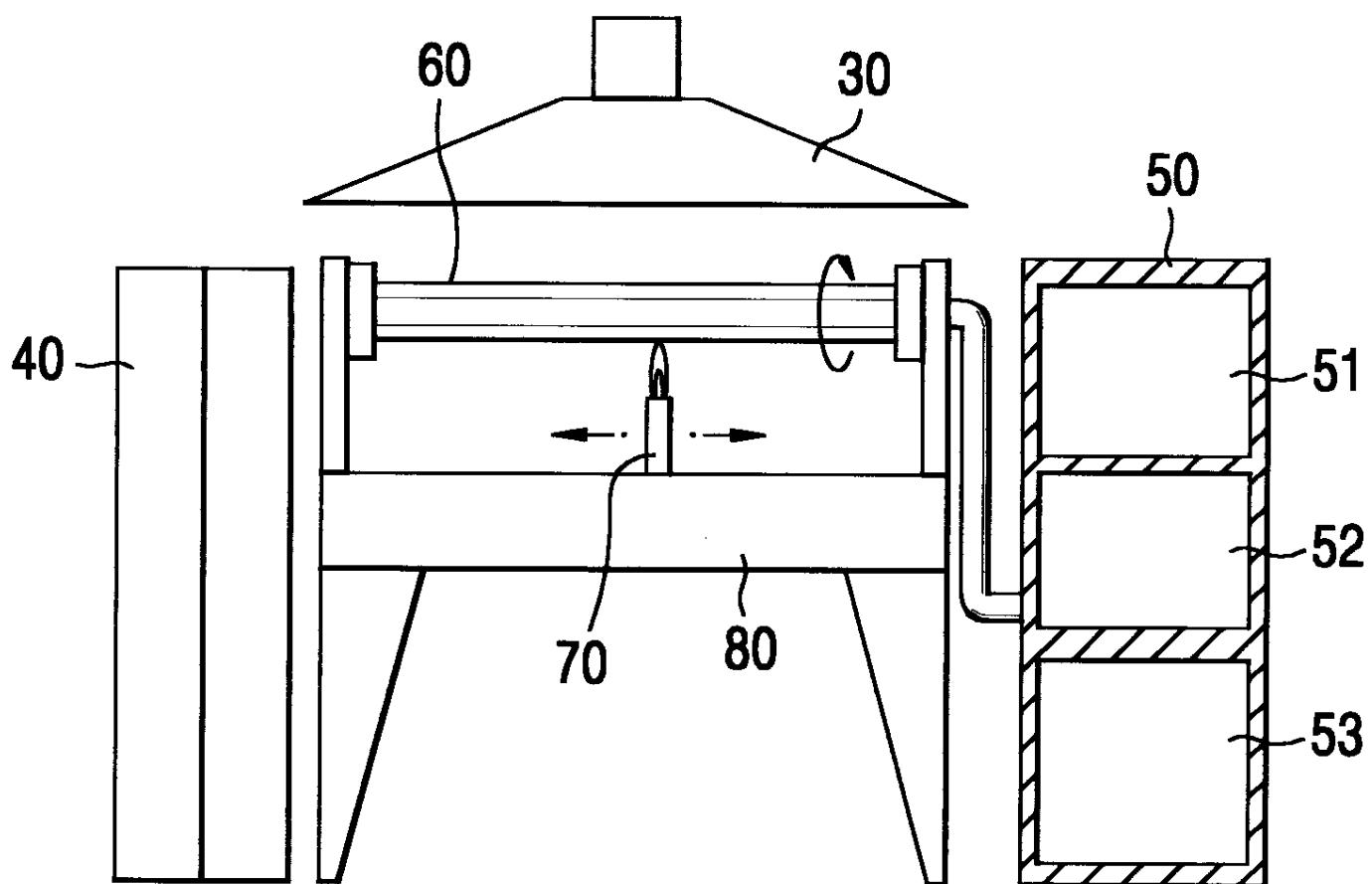
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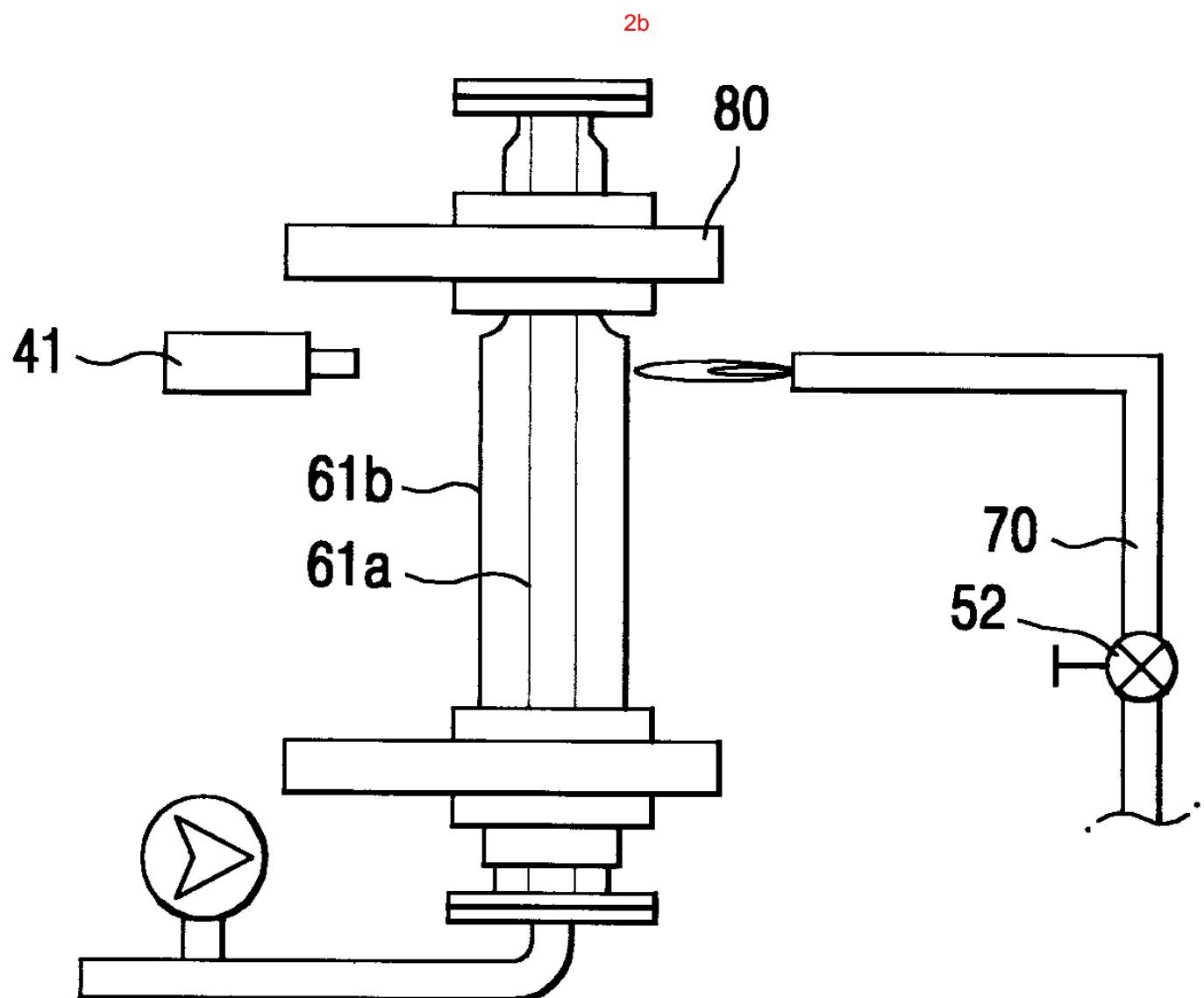
2

1



2a





3

